

Product data sheet

# 1. General description

Ultrafast power diode in a SOD113 (TO-220F) plastic package.

### 2. Features and benefits

- Low on-state loss
- Ultra low leakage
- Low switching loss
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance

# 3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

# 4. Quick reference data

Table	1	Quick	reference	data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>h</sub> ≤ 71 °C; square-wave; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	-	15	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>h</sub> ≤ 71 °C; square-wave	-	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sinusoidal waveform; <u>Fig. 4</u>	-	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sinusoidal waveform	-	-	165	A
Static charac	teristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.1	1.38	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	0.96	1.25	V
Dynamic cha	racteristics	·				
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	50	60	ns

# 5. Pinning information

Table 2. I	Table 2. Pinning information									
Pin	Symbol	Description	Simplified outline	Graphic symbol						
1	К	cathode	mb	К — К — А						
2	А	anode		001aaa020						
mb	n.c.	mounting base; isolated	TO-220F (SOD113)							

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYT79X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BYT79X-600P	BYT79X-600P

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 71 °C; square-wave; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	15	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 71 \ ^\circ C;$ squarewave	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sinusoidal waveform; <u>Fig. 4</u>	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sinusoidal waveform	-	165	A
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

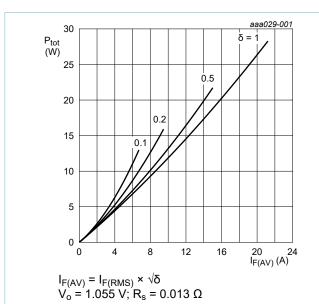
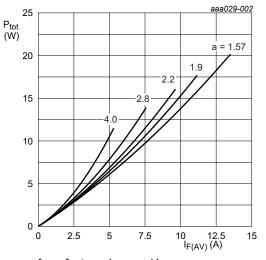


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



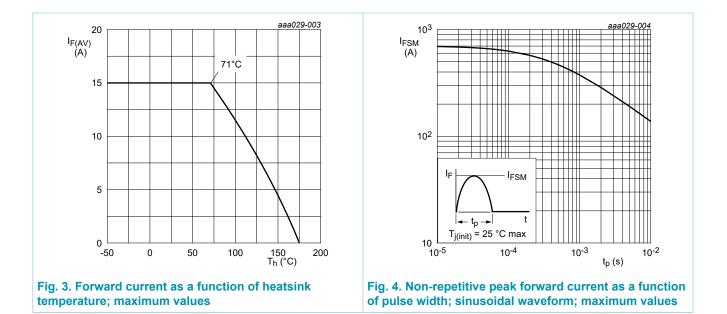
a = form factor = I  $_{F(RMS)}$  / I  $_{F(AV)}$  V  $_o$  = 1.055 V; R  $_s$  = 0.013  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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# **BYT79X-600P**

### Ultrafast recovery diode

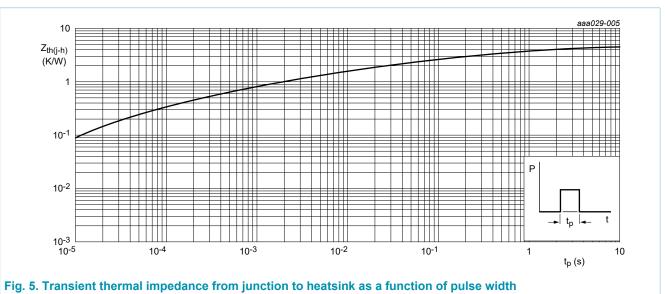


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Ultrafast recovery diode

### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



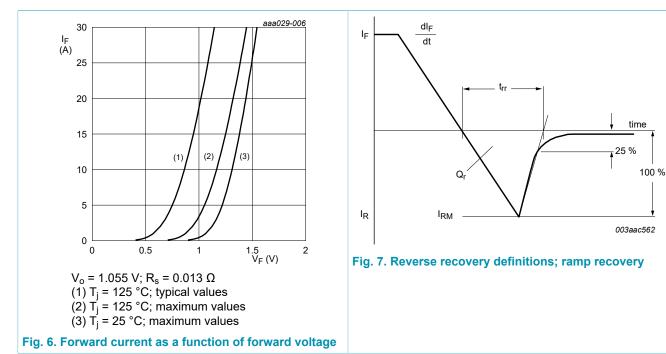
### **10. Isolation characteristics**

Fable 7. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink		-	10	-	pF

Ultrafast recovery diode

### **11. Characteristics**

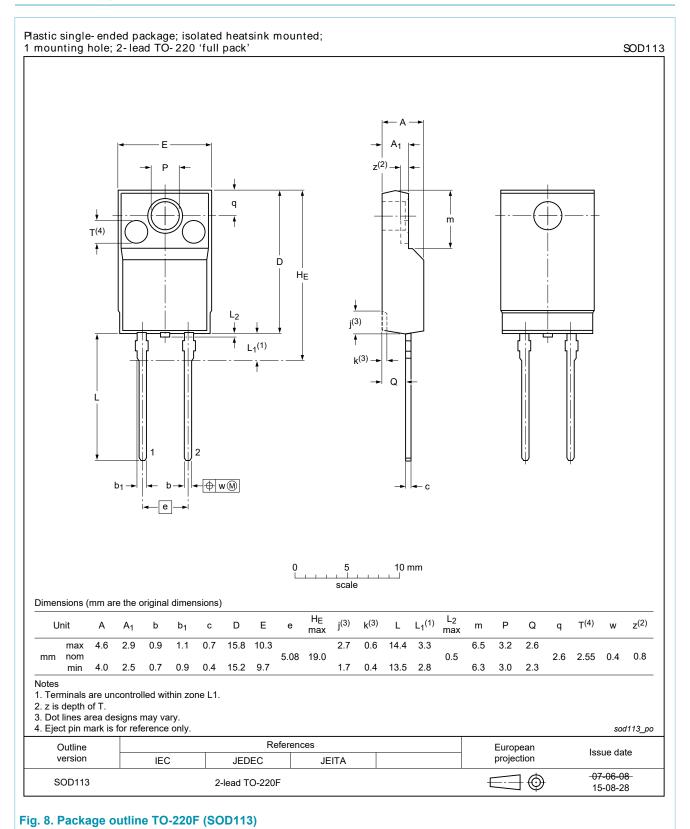
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.1	1.38	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	0.96	1.25	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	1	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	80	200	μA
Dynamic ch	naracteristics	· · ·				
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 100 ^{\circ}\text{C}$	-	3	-	A
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	60	-	nC
		I <sub>F</sub> = 2 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 20 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>	-	60	110	nC





**Ultrafast recovery diode** 

### **12. Package outline**



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#### **Ultrafast recovery diode**

# 13. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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